

Ref #	Hits	Search Query	DBs	Default Operat or	Plural s	Time Stamp
L1	814	(wafer substrate) with ((etch\$3 with (angle\$2 tilt\$2 oblique)) with (mask\$3 photoresist\$4 resist\$3))	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/02/10 13:42
L2	814	1 and ((etch\$3 with (angle\$2 tilt\$2 oblique)) with (mask\$3 photoresist\$4 resist\$3))	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/02/10 14:46
L3	324	2 and ((dielectric insulat\$4) with (mask\$3 photoresist\$4 resist\$3))	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/02/10 14:47
L4	193	3 and ((plasma ion) near3 etch\$3)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/02/10 14:48
L5	19	4 and ((cap capping) near4 layer)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/02/10 14:50